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## Particle beam profilers based on fluence dependent variations of carrier lifetime and scintillation intensity in Si and GaN materials

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The particle beam profilers, based on fluence measurements performed by recording the changes of carrier lifetime in Si material and scintillation intensity of thin GaN layers, caused by radiation induced defects and emission centres, will be presented. The beams of penetrative (26 GeV/c) and stopped (1.6 MeV) protons will be discussed.

**Author:** CEPONIS, Tomas (nstitute of Photonics and Nanotechnology, Vilnius University)

**Presenter:** CEPONIS, Tomas (nstitute of Photonics and Nanotechnology, Vilnius University)

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